

2-22GHz, 13dB Gain Low-Noise Wideband Distributed Amplifier

Features

- >15dBm P_{1dB} with 1.8dB NF and 13dB gain at 10GHz
- Gain flatness ~ +/-0.75dB
- <2dB NF from 6-12GHz
- Single supply voltage of +5V @ 50mA
- Input and Output matched to 50Ω
- 1.5mm x 2.82mm x 0.1mm die size

Applications

- Instrumentation
- Electronic warfare
- Microwave communications
- Radar







Typical Performance (CW, Typical Device, RF Probe): $T_A = 25^{\circ}C$, $V_{DD} = 5V$

Parameter	Min	Тур	Max	Units
Frequency	2	-	22	GHz
Small Signal Gain	12.5	-	14.0	dB
Noise Figure	1.8	2.5	4.0	dB
Output Power, P _{1dB}	10	13	16	dBm
Output Power, P _{3dB}	12	15	18	dBm
Output IP3	19	26	31	dBm
Drain Current		50		mA



Table 1: Absolute Maximum Ratings, Not Simultaneous

Parameter	Rating	Units
Drain Voltage (V _D)	+8	V
Input Power (P _{IN})	24	dBm
Channel Temperature (T _c)	150 ¹	°C
Operating Ambient Temperature (T _A)	-55 to +85	°C
Storage Temperature	-65 to +150	°C
Thermal Resistance, Channel to Die Backside	40	°C/W



Caution, ESD Sensitive Device

 1 MTTF > 10⁸ hours at T_c = 150°C

Table 2: Specifications (CW, 100% Test): $T_A = 25^{\circ}C$, $V_{DD} = 5V$, $I_{DD} = 65mA$

Parameter	Frequency	Min	Max	Units
I _{DD}	-	-	90	mA
Small Signal Gain	20GHz	11.0	-	dB
Output Power, P _{1dB}	20GHz	8.5	-	dBm

RF Probe Measurement Set-Up With Reference Planes²



² Reference planes are the same for S-parameter files downloadable on www.microsemi.com/mmics



Typical Performance, RF Probe V_{DD} = 5V, I_{DD} = 50mA, T_A = 25°C unless otherwise noted





NF Over Temperature





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Typical Performance, RF Probe $V_{DD} = 5V$, $I_{DD} = 50$ mA, $T_A = 25^{\circ}$ C unless otherwise noted





Power Sweep Over Frequency









Typical Performance, Connectorized Test Fixture $V_{DD} = 5V$, $I_{DD} = 50$ mA, $T_A = 25^{\circ}$ C unless otherwise noted



S₂₁ Over Temperature





S₂₂ Over Temperature 0 - +25°C· -40°C-+85°C -5 -10 (g) -15 (g) -20 S -25 -25 -30 -35 -40 20 22 2 4 6 8 10 12 14 16 18 Frequency (GHz)

NF Over Temperature





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Typical Performance, Connectorized Test Fixture

 V_{DD} = 5V, I_{DD} = 50mA, T_A = 25°C unless otherwise noted



Power Sweep, +85°C



OIP3, P_{out}/tone = 3dBm



Power Sweep, +25°C 18 -4GHz -8GHz 2GHz -6GHz -10GHz 17 -12GHz -14GHz -16GHz -18GHz -20GHz 16 15 Gain (dB) 14 13 12 11 10 9 8 ·25° Ċ 7 2 4 6 8 10 12 14 16 18 20 P_{OUT} (dBm)







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Typical Performance, Connectorized Test Fixture

 V_{DD} = 5V, I_{DD} = 50mA, T_A = 25°C unless otherwise noted









Chip layout showing pad locations.

All dimensions are in microns. Die thickness is 100 microns. Backside metal is gold, bond pad metal is gold. Refer to Die Handling Application Note MM-APP-0001 (visit www.microsemi.com/mmics).



Table 3: Pad Descriptions

Pad #	Descrtiption	Pad Dimensions (µm)
1, 3, 6	Ground	100 x 100
2	RF_{IN} , Pad is AC Coupled	100 x 190
5	RF _{OUT} , Pad is AC Coupled	100 x 190
4	V _{DD}	100 x 100

Biasing

MMA003AA is a self-biased device with single positive supply. Apply V_{DD} to pad 4.



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